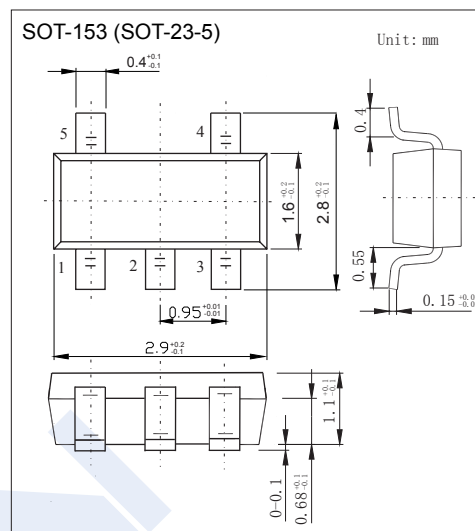
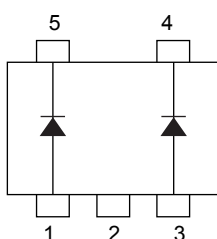


Schottky Diodes

SBE807 (KBE807)

■ Features

- Low switching noise.
- Low reverse current
- High frequency rectification

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Nonrepetitive Peak Reverse Surge Voltage	V_{RSM}	35	
Average Output Current	I_o	1	A
Surge Forward Current @ 50Hz	I_{FSM}	10	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	111	$^\circ\text{C/W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 0.2\text{mA}$	30			V
Forward voltage	V_F	$I_F = 0.7\text{A}$			0.5	
		$I_F = 1\text{A}$			0.53	
Reverse voltage leakage current	I_R	$V_R = 16\text{V}$			15	μA
Junction capacitance	C_j	$V_R = 10\text{V}, f = 1\text{MHz}$		27		pF
Reverse recovery time	t_{rr}	$I_F = I_R = 100\text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$			10	ns

■ Marking

Marking	SJ
---------	----

Schottky Diodes

SBE807 (KBE807)

■ Typical Characteristics

